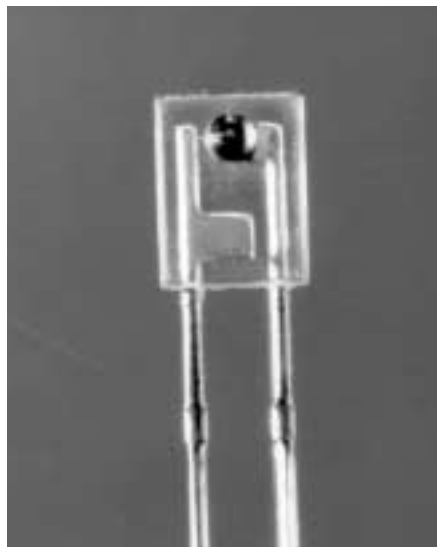


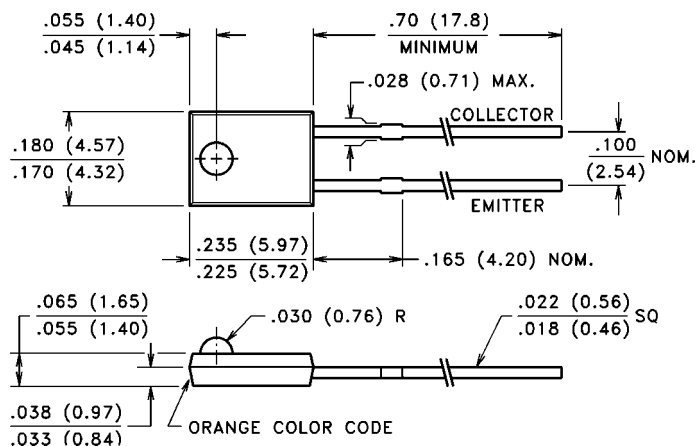
.025" NPN Phototransistors

Molded Lensed Lateral Package

VTT7122, 7123, 7125



PACKAGE DIMENSIONS inch (mm)



CASE 7 LATERAL
CHIP TYPE: 25T

PRODUCT DESCRIPTION

A small area high speed NPN silicon phototransistor mounted in a lensed, side looking, transparent plastic, transfer molded package. These devices are spectrally and mechanically matched to the VTE717x series of IREDs.

ABSOLUTE MAXIMUM RATINGS ■

(@ 25°C unless otherwise noted)

Maximum Temperatures

Storage Temperature: -40°C to 85°C

Operating Temperature: -40°C to 85°C

Continuous Power Dissipation: 50 mW

Derate above 30°C: 0.91 mW/°C

Maximum Current: 25 mA

Lead Soldering Temperature: 260°C
(1.6 mm from case, 5 sec. max.)

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also typical curves, pages 91-92)

Part Number ■	Light Current			Dark Current		Collector Breakdown	Emitter Breakdown	Saturation Voltage	Rise/Fall Time	Angular Response $\theta_{1/2}$
	I_C			I_{CEO}		$V_{BR(CEO)}$	$V_{BR(ECO)}$	$V_{CE(SAT)}$	t_R/t_F	
	mA		H fc (mW/cm ²) $V_{CE} = 5.0$ V	$H = 0$		$I_C = 100 \mu A$ $H = 0$	$I_E = 100 \mu A$ $H = 0$	$I_C = 1.0$ mA $H = 400$ fc	$I_C = 1.0$ mA $R_L = 100 \Omega$	
	Min.	Max.		(nA) Max.	V_{CE} (Volts)	Volts, Min.	Volts, Min.	Volts, Max.	μ sec, Typ.	Typ.
VTT7122	1.0	—	100 (5)	100	10	30	5.0	0.25	2.0	±36°
VTT7123	2.0	—	100 (5)	100	10	30	5.0	0.25	2.0	±36°
VTT7125	4.5	—	100 (5)	100	10	30	5.0	0.25	2.0	±36°

■ Refer to General Product Notes, page 2.